NSN 5962-01-385-0620

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View Online at https://aerobasegroup.com/nsn/5962-01-385-0620

Body Length:

Between 1.040 inches and 1.060 inches

Body Width:

Between 0.290 inches and 0.310 inches

Body Height:

Between 0.180 inches and 0.200 inches

Maximum Power Dissipation Rating:

300.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Pacer dawn

Features Provided:

Bipolar and burn in, mil-std-883, class b and electrostatic sensitive and hermetically sealed and inverted output and programmed and tested to mil-std-883

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

16 input

Criticality Code Justification:

Feat

Case Outline Source And Designator:

D-8 mil-m-38510

Current Rating Per Characteristic:

1.00 milliamperes reverse current, dc microamperes and 50.00 milliamperes reverse current, dc absolute

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, digital, bipolar, programmable array logic

Voltage Rating And Type Per Characteristic:

-1.5 volts input and 5.5 volts input and -0.5 volts power source and 12.0 volts power source

Time Rating Per Chacteristic:

75.00 nanoseconds input to output access

Memory Device Type:

Pal

Special Features:

Esd; altered item programmed using 14933 8506501rx using vdd0236.02.00; clock frequency is 8 mhz

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Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A458a0